

**TECHNICAL DATA**  
**DATA SHEET 602, REV -**

**HERMETIC POWER MOSFET**  
**N-CHANNEL**

**FEATURES:**

- 100 Volt, 0.18 Ohm, 7.4A MOSFET
- Fast Switching
- Low  $R_{DS(on)}$
- Equivalent to IRFE130

**MAXIMUM RATINGS**

ALL RATINGS ARE AT  $T_C = 25^\circ\text{C}$  UNLESS OTHERWISE SPECIFIED.

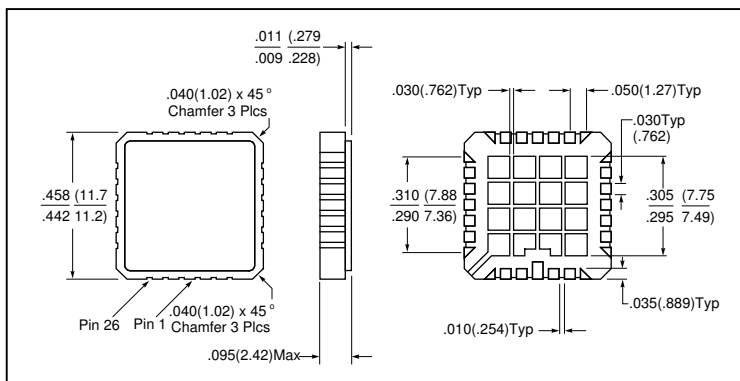
RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
GATE TO SOURCE VOLTAGE	$V_{GS}$	-	-	$\pm 20$	Volts
ON-STATE DRAIN CURRENT @ $T_C = 25^\circ\text{C}$	$I_D$	-	-	10.8	Amps
ON-STATE DRAIN CURRENT @ $T_C = 100^\circ\text{C}$	$I_D$	-	-	6.8	Amps
OPERATING AND STORAGE TEMPERATURE	$T_{OP}/T_{STG}$	-55	-	+150	$^\circ\text{C}$
TOTAL DEVICE DISSIPATION @ $T_C = 25^\circ\text{C}$	$P_D$	-	-	42	Watts
THERMAL RESISTANCE, JUNCTION TO CASE	$R_{thJC}$	-	-	3.0	$^\circ\text{C}/\text{W}$

**ELECTRICAL CHARACTERISTICS**

DRAIN TO SOURCE BREAKDOWN VOLTAGE $V_{GS} = 0\text{V}, I_D = 1.0\text{mA}$	$BV_{DSS}$	100	-	-	Volts
STATIC DRAIN TO SOURCE ON STATE RESISTANCE $V_{GS} = 10\text{V}, I_D = 5.4\text{A}$	$R_{DS(ON)}$	-	-	0.18	$\Omega$
GATE THRESHOLD VOLTAGE $V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	$V_{GS(th)}$	2.0	-	4.0	Volts
FORWARD TRANSCONDUCTANCE $V_{DS} = 15\text{V}, I_{DS} = 6.8\text{A}$	$g_{fs}$	3.0	-	-	$\text{S}(1/\Omega)$
ZERO GATE VOLTAGE DRAIN CURRENT $V_{DS} = 0.8 \times \text{Max. Rating}, V_{GS} = 0\text{V}$ $V_{DS} = 0.8 \times \text{Max. Rating}, V_{GS} = 0\text{V}, T_J = 125^\circ\text{C}$	$I_{DSS}$	-	-	25 250	$\mu\text{A}$
GATE TO SOURCE LEAKAGE FORWARD $V_{GS} = 20\text{V}$ GATE TO SOURCE LEAKAGE REVERSE $V_{GS} = -20\text{V}$	$I_{GSS}$	-	-	100 -100	nA
TURN ON DELAY TIME RISE TIME TURN OFF DELAY TIME FALL TIME $V_{DD} = 50\text{V}, I_D = 10.8\text{A}, R_G = 7.5\Omega$	$t_{d(ON)}$ $t_r$ $t_{d(OFF)}$ $t_f$	-	-	30 75 40 45	nsec
TOTAL GATE CHARGE $I_D = 10.8\text{A},$ GATE TO SOURCE CHARGE $V_{GS} = 10\text{V},$ GATE TO DRAIN CHARGE $V_{DS} = 0.5 \times \text{Max. Rating}$	$Q_g$ $Q_{gs}$ $Q_{gd}$	12.8	-	28.5 6.3 16.6	nC
DIODE FORWARD VOLTAGE $T_C = 25^\circ\text{C}, I_S = 10.8\text{A}, V_{GS} = 0\text{V}$	$V_{SD}$	-	-	1.5	Volts
REVERSE RECOVERY CHARGE $T_J = 25^\circ\text{C}, di/dt \leq 100\text{A}/\mu\text{sec}, V_{DD} \leq 50\text{V}$	$Q_{RR}$	-	-	3.0	$\mu\text{C}$
REVERSE RECOVERY TIME $T_J = 25^\circ\text{C}, I_F = 10.8\text{A}, di/dt \leq 100\text{A}/\mu\text{sec}, V_{DD} \leq 50\text{V}$	$t_{rr}$	-	-	300	nsec
INPUT CAPACITANCE $V_{GS} = 0\text{V}$ OUTPUT CAPACITANCE $V_{DS} = 25\text{V}$ REVERSE TRANSFER CAPACITANCE $f = 1.0\text{MHz}$	$C_{iss}$ $C_{oss}$ $C_{rss}$	-	650 240 44	-	pF

**SENSITRON**  
**DATA SHEET 602**  
**REVISION -**

**MECHANICAL DIMENSIONS: in Inches / m**



**LCC-28T**

**PINOUT TABLE**

Device Type	PIN(S) 1 & 15-28	PINS 5-11	PINS 2,3,13,14
Single MOSFET in a LCC-28T Package	SOURCE	DRAIN	GATE

**TECHNICAL DATA**

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